

## IN THE SPECIFICATION

Please amend the third paragraph on page 3 as follows:

In accordance with an example reported in the above specification, it is shown that, for a 6-inch diameter wafer which is cleaned for 60 min with the Standard Cleaning - 1 (hereinafter referred to as "SC - 1"), which is made by using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$  the surface density of particles having a diameter of not less than  $0.13 \mu\text{m}$  is about 1200 counts/cm<sup>2</sup> when nitrogen is not doped, whereas it becomes about 1/20 of the above surface density when nitrogen is doped. In accordance with the description of the example, it is estimated that the surface density of particles having a size of not less than  $0.13 \mu\text{m}$  is not more than 60 counts/cm<sup>2</sup>. In recent years, a wafer having such a greater surface density as in this estimation can hardly be used as a wafer for manufacturing devices.